

**IN THE SPECIFICATION:**

On page 2, please amend the last paragraph which continues on page 3 as follows:

B1  
A red-light-emitting semiconductor laser structure is usually a multilayer structure made up of quaternary mixed crystals  $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$   $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$  (where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$ ), which will be herein simply labeled as AlGaIP), which consist essentially of Al, Ga, In and P. And an infrared semiconductor laser structure is usually a multilayer structure made up of ternary mixed crystals  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  (where  $0 \leq z \leq 1$ ), which will be herein simply labeled as AlGaAs), which consist essentially of Al, Ga and As.

On page 11, please amend the fourth paragraph as follows:

B2  
In the inventive method for fabricating a semiconductor laser device, the etching control layer is preferably made of  $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$   $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$  (where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$ ) and the first multilayer structure preferably includes semiconductor layers made of  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  (where  $0 \leq z \leq 1$ ).

On page 12, please amend the first paragraph as follows:

B3  
In the inventive method for fabricating a semiconductor laser device, the etching control layer is preferably made of  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  (where  $0 \leq z \leq 1$ ) and the first multilayer structure preferably includes semiconductor layers made of  $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$   $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$  (where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$ ).

On page 15, please amend the third paragraph as follows:

B4  
In the inventive semiconductor laser device, the etching control layer is preferably made of  $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$   $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$  (where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$ ) and the first semiconductor laser structure preferably includes semiconductor layers made of  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  (where  $0 \leq z \leq 1$ ).

On page 15, please amend the fifth paragraph which continues onto page 16 as follows:

B6  
In the inventive semiconductor laser device, the etching control layer is preferably made of  $\text{Al}_z\text{Ga}_{1-z}\text{As}$  (where  $0 \leq z \leq 1$ ) and the first multilayer structure preferably includes semiconductor layers made of  $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$   $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$  (where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$ ).